

AMENDMENTS TO THE SPECIFICATION:

Please amend the Specification as follows.

Please delete the eighteen paragraphs beginning on page 5, line 16 and ending on page 18, line 25.

Please insert the following paragraph on page 5, line 16 after “BRIEF SUMMARY OF THE INVENTION.”

A semiconductor device according to an aspect of the present invention comprises: a semiconductor substrate of a first conductivity type; a convex semiconductor layer of the first conductivity type on the semiconductor substrate; a source region and a drain region of a second conductivity type in the convex semiconductor layer; a gate insulator on side surfaces of the convex semiconductor layer and a top surface of the convex semiconductor layer; a gate electrode on a portion of the gate insulator between the source region and the drain region; and a trench capacitor in the semiconductor substrate, the trench capacitor connected to one of the source and drain regions.